

# Isotropic plasma-thermal atomic layer etching of aluminum nitride using SF<sub>6</sub> plasma and Al(CH<sub>3</sub>)<sub>3</sub>

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## Abstract

We report the isotropic plasma atomic layer etching (ALE) of aluminum nitride using sequential exposures of SF<sub>6</sub> plasma and trimethylaluminum (Al(CH<sub>3</sub>)<sub>3</sub>, TMA). ALE was observed at temperatures greater than 200 °C, with a maximum etch rate of 1.9 Å/cycle observed at 300 °C as measured using ex-situ ellipsometry. After ALE, the etched surface was found to contain a lower concentration of oxygen compared to the original surface and exhibited a  $\sim 35\%$  decrease in surface roughness. These findings have relevance for applications of AlN in nonlinear photonics and wide bandgap semiconductor devices.

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Aluminum nitride (AlN) is a III–V semiconductor of interest in photonics and electronics owing to its simultaneous strong second-order ( $\chi^{(2)}$ ) and third-order ( $\chi^{(3)}$ ) optical nonlinearities, wide bandgap ( $> 6$  eV), and high dielectric constant ( $\sim 8.9$ ) [1–3]. AlN has the lowest optical loss among III–V group materials over a range of wavelengths from the ultraviolet to the mid-infrared [2, 4] and is under investigation for applications in ultraviolet light emitting diodes [5, 6] and optical quantum circuits [7, 8]. High quality factors ( $\gtrsim 10^6$ ) have been achieved in AlN microring resonators [9, 10] which are fundamental components of on-chip frequency combs and second-harmonic generation elements [11–13]. AlN also finds potential applications as a low-leakage gate dielectric [14–17] and has been employed in various thin film transistors [18–20].

For these applications, limitations on figures of merit have been attributed to microfabrication processes. For instance, the presence of a native oxide leads to unstable etch rates with dry etching processes [21]. The surface and sidewall roughness of etched nanostructures is on the order of 1 – 4 nm [1, 9, 22], leading to light scattering. Poor-quality surface material with a refractive index fluctuations may also lead to light scattering even on nominally smooth surfaces. These mechanisms lead to waveguide loss and limit the quality factor of optical microresonators, which in turn affects the performance of on-chip photonic devices [23].

Atomic layer etching (ALE) is an emerging subtractive nanofabrication process with the potential to address these limitations [24–27]. In isotropic ALE, a surface is etched using sequential reactions consisting of an initial surface modification followed by volatilization of the modified surface layer. Early development of ALE focused on directional etching using bombardment of a suitably prepared surface with low energy ions or neutral atoms [28–30]. Recently, isotropic ALE processes have been developed which enable isotropic etching with Angstrom-scale precision [25]. Thermal and plasma isotropic ALE recipes are now available for various dielectrics and semiconductors including  $\text{Al}_2\text{O}_3$  [31–36],  $\text{SiO}_2$  [37, 38], InGaAs [39], and others [25, 40, 41]. Surface smoothing of etched surfaces using ALE has been reported for various materials including  $\text{Al}_2\text{O}_3$  [34, 42], amorphous carbon [43], and III–V semiconductors [39, 44]. For AlN, isotropic ALE recipes have been reported using  $\text{HF}/\text{Sn}(\text{acac})_2$  and  $\text{HF}/\text{BCl}_3$  [45, 46]. However, identifying alternate reactants to HF vapor as well as realizing higher etch rates remain of interest for ALE of AlN.

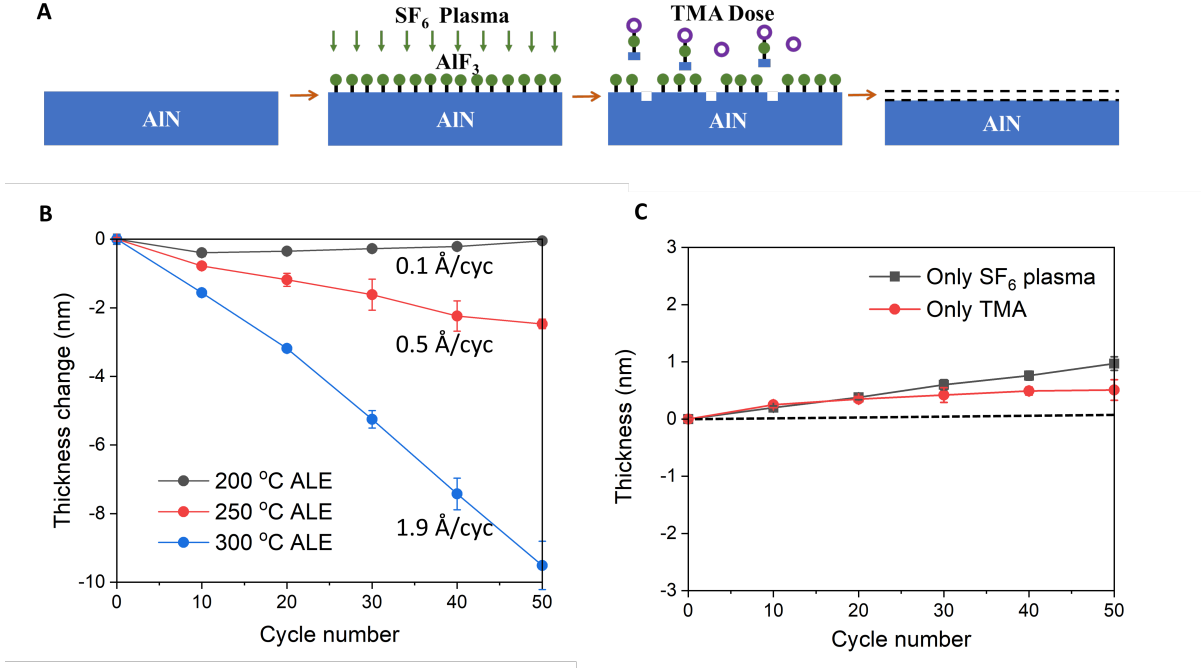
Here, we report the atomic layer etching of AlN using sequential exposures of  $\text{SF}_6$  plasma

and trimethylaluminum ( $\text{Al}(\text{CH}_3)_3$ , TMA), achieving up to 1.9 Å/cycle at 300 °C. The necessity of both half-reactions for etching was established by verifying that no etching occurred with only  $\text{SF}_6$  plasma or TMA. The etched surface was characterized using atomic force microscopy and x-ray photoemission spectroscopy. The etched surface exhibited a decrease in roughness by  $\sim 35\%$  over a range of spatial frequencies after 50 cycles of ALE, and the ALE process was found to reduce the native oxide concentration at the surface. These improved surface characteristics highlight the potential of the process for applications in photonics and wide bandgap electronics.

The sequence for the plasma-assisted thermal ALE process is illustrated in Fig. 1(A).  $\text{SF}_6$  plasma is first generated to fluorinate the surface using F radicals, producing  $\text{AlF}_3$  on the AlN film surface. The excess gas phase reactants are then purged, and a TMA dose is introduced and held in the chamber. The TMA reacts with the  $\text{AlF}_3$  in a ligand-exchange reaction, yielding volatile etching products [47]. We hypothesize that the surface chemical reactions are similar to those reported for the isotropic plasma ALE of alumina using the same reactants [36]; the specific reactions are a topic of future study.

This process was applied to AlN samples grown on Si (111) wafers by sputtering of an Al target gun with flow of 10 sccm nitrogen and 20 sccm Ar. The initial AlN films had a thickness of 280 Å as measured by spectroscopic ellipsometry (J. A. Woolam) at 65°, 70° and 75° from 370 nm to 1000 nm. The samples were  $12 \times 12 \text{ mm}^2$  chips. To determine the thickness change after a certain number of ALE cycles, 9 points were measured using ellipsometry on each AlN sample using a pre-programmed  $10 \times 10 \text{ mm}^2$  square array with 5 mm spacing between points. Subsequently, the spectrum was fit by the Cauchy model to obtain the AlN thickness. The average thickness of a single sample was calculated using thicknesses measured and modeled by the 9 points.

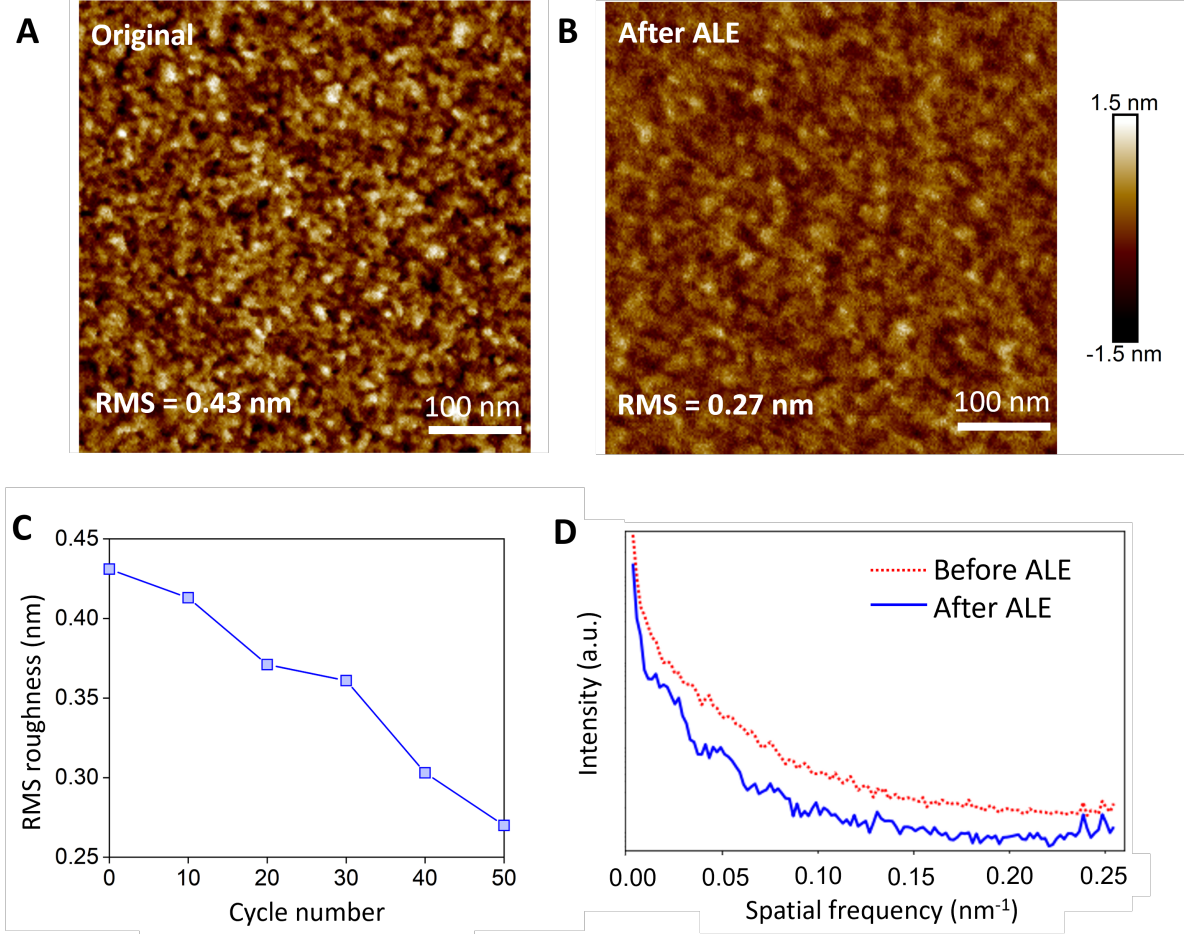
Isotropic plasma ALE was performed using a FlexAL atomic layer deposition system (Oxford Instruments). The sample was placed on a 6-inch Si carrier wafer. The walls of the chamber were held at  $\sim 150$  °C to minimize reactant condensation.  $\text{SF}_6$  plasma and trimethylaluminium (TMA) were used as the reactants.  $\text{SF}_6$  plasma was struck with 30 sccm  $\text{SF}_6$  and 150 sccm Ar mixing gas for 1 s and stabilized at 100 W power with 50 sccm  $\text{SF}_6$  and 150 sccm Ar mixing gas for 2 s. The TMA was dosed with 100 sccm Ar carrier gas for 1 s. The precursor was then held in the chamber for 20 s without flowing gas or purging. The stage temperature was set at 200, 250, and 300 °C. X-ray Photoemission Spectroscopy



**Figure 1.** (a) Isotropic plasma ALE of AlN. A low-power (100 W)  $\text{SF}_6$  plasma containing F radicals (green dots) is first used to fluorinate the surface. TMA (purple circles) is introduced to perform ligand exchange with  $\text{AlF}_3$ , yielding isotropic etching. (b) AlN thickness versus cycle number at different temperatures. The EPC is calculated based on the change in thickness after 50 cycles. (c) Thickness change versus cycle number for  $\text{SF}_6$  plasma only and TMA-only recipes at 300 °C, confirming that etching requires both steps of the ALE process. Lines are guides to the eye. Error bars are as indicated or the size of the symbol.

(XPS) analysis was performed using a Kratos Ultra x-ray photoelectron spectrometer using a monochromatic Al  $K\alpha$  source (Kratos Analytical). The XPS data were analyzed in CASAXPS (Casa Software, Ltd.).

Figure 1(B) shows the AlN film thickness change versus cycle number for different process temperatures with other parameters fixed. At 200 °C, we observe an initial etch in the first 10 cycles followed by a subsequent thickness increase, with an overall etch rate of 0.1 Å/cycle over 50 cycles. At 250 °C, a monotonic trend of thickness change is observed with an EPC of 0.5 Å/cycle. The maximum EPC of 1.9 Å/cycle was achieved at 300 °C. The EPC increase with temperature is generally consistent with prior thermal ALE studies [25] and those using the isotropic plasma ALE approach employed here [36].



**Figure 2.** Smoothing effect of isotropic plasma ALE. AFM image of (a) original surface and (b) after 50 cycles of ALE at 300 °C. The root mean square (RMS) roughness is calculated and labeled in the images. (c) Surface roughness versus ALE cycle number, indicating a monotonic decrease in roughness with cycle number. Lines are guides to the eye. (d) Surface PSD versus spatial frequency for the original sample (blue solid line) and the etched sample (orange solid line). The etching uniformly decreases surface roughness at all spatial frequencies.

To confirm that both half-reactions are required for etching, in Fig. 1(C) we show the measured thickness change versus cycle number for SF<sub>6</sub>-plasma-only and TMA-only processes at 300°C. No etching is observed with either recipe. These results support the proposed atomic layer etching mechanism requiring both half-reactions.

We next characterized the surface roughness of the film before and after ALE using Atomic Force Microscopy (AFM). Figures 2(A) and 2(B) show AFM images of the film before and

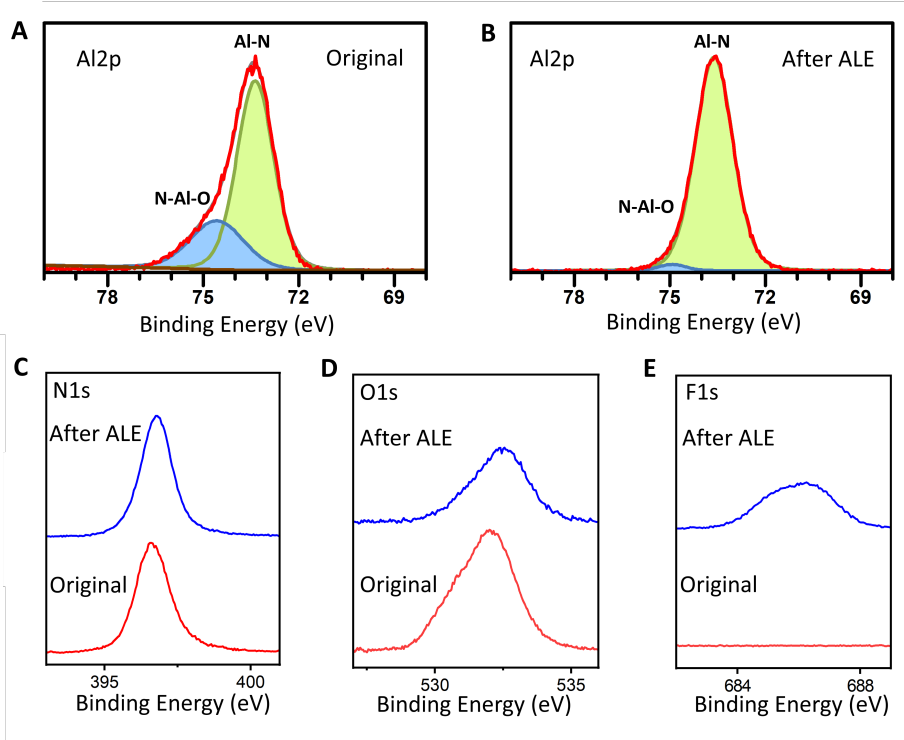
after ALE at 300 °C, respectively. Over an area of  $0.5 \times 0.5 \mu\text{m}^2$ , the RMS roughness decreased  $\sim 35\%$ , from 0.43 nm to 0.27 nm, after 50 cycles of ALE. The RMS roughness versus cycle number is plotted in Fig. 2(C). A monotonic decrease in surface roughness is observed with cycle number. This observation was reproduced on three separate regions on each sample.

The power spectral density (PSD) of the surface was computed using the measured AFM scans. The PSD provides a quantitative measure of the lateral distance over which the surface profile varies in terms of spatial frequencies [48–51]. The PSD was calculated by removing tilt via linear plane-fit and subsequently performing a 1D-discrete Fourier transform over each row and column in the raw AFM data. The transformed data were then averaged along one dimension to produce single PSD curve. The PSD computed from Figs. 2(A) and 2(B) are plotted in Fig. 2(D). A uniform decrease in roughness is observed over all spatial frequencies, indicating that both high and low spatial frequency components are smoothed by the ALE process.

The chemical changes in the film composition due to ALE were characterized by XPS. The XPS core levels for the Al2p, N1s, and O1s peaks were recorded before and after the ALE process. The spectra were fit using a Gaussian-Lorentzian function and then calibrated with the C1s position at 285 eV. For Al2p (Figs. 3(A) and 3(B)), two peaks are identified at 73.4 eV and 74.5 eV, corresponding to Al–N bonds and native oxide N–Al–O bonds, respectively. These values are consistent with those reported in the literature for AlN films [52–54].

After ALE, the atomic percentage ratio between the Al2p N–Al and the total Al2p is increased from 73% to 98%. In Figs. 3(D), 3(C) and 3(E), we plot the N1s, O1s and F1s spectra, respectively, to compare the surface chemistry before and after ALE. We observe an 11% intensity enhancement of the N1s peak after ALE, while the O1s intensity decreases 42%. We also observe the appearance of an F1s peak after ALE, indicating the presence of residual fluorine in the surface. However, an Al–F peak is not observed in Fig. 3(B), suggesting that the residual F is physisorbed rather than chemically attached to the surface. After ALE, the atomic composition of O decreased from 18% to 11%, while the F composition increased from 0 to 10%. These observations indicate that the surface native oxide concentration is reduced in the ALE process.

We now discuss the characteristics of our isotropic plasma ALE process in context with



**Figure 3.** Surface chemical composition as characterized by XPS. (a) Al2p XPS spectra of the original surface, indicating the presence of oxygen by the N-Al-O peak. (b) Corresponding spectrum after 30 ALE cycles. The N-Al-O component is reduced compared with (a). XPS spectra of (c) N1s, (d) O1s and (e) F1s spectra before and after ALE treatment. The shape of the N1s spectrum remains the same after ALE but the N intensity increases. The O1s intensity is decreased after ALE treatment, consistent with the reduction in the N-Al-O peak observed in (b). An F1s peak appears after ALE. For all the plots, y-axis is the XPS intensity and x-axis is the binding energy.

thermal ALE processes for AlN and related materials. Thermal ALE of AlN has been reported previously using HF and  $\text{Sn}(\text{acac})_2$  [45] and HF or  $\text{XeF}_2$  and  $\text{BCl}_3$  [46]. The maximum EPC reported for the latter process was  $0.93 \text{ \AA}$  at a substrate temperature of  $300 \text{ }^\circ\text{C}$  [46]. Neglecting possible differences between stage and substrate temperatures, the present process achieves a nearly two-fold increase in EPC at a comparable temperature. The present process also enables similar EPCs as the thermal process at lower temperatures. Similar observations regarding higher etch rates at a given temperature using an isotropic plasma ALE process was reported in Ref. [36] for etching of alumina with the same reactants. These observations offer evidence for the benefits of isotropic plasma ALE processes compared with

purely thermal methods.

Our isotropic plasma ALE process may find potential applications in on-chip nonlinear and quantum photonics based on AlN, for which scattering by surface imperfections represents a primary limitation for various figures of merit. Based on the measured PSD, our process decreases surface roughness of features with periods up to tens of nanometers. This smoothing capability may enable the reduction in sidewall roughness due to reactive ion etching as well as lithographic roughness transferred from the resist to the film, which would in turn reduce optical losses.

In summary, we reported an isotropic plasma ALE process for AlN using sequential  $\text{SF}_6$  plasma and  $\text{Al}(\text{CH}_3)_3$  exposures. The etch rate reaches a maximum of  $1.9 \text{ \AA}/\text{cycle}$  at  $300^\circ\text{C}$ . We observe a smoothing effect from ALE, with a decrease in RMS roughness of  $\sim 35\%$  after 50 cycles. The surface oxygen content is significantly decreased after ALE, indicating that native oxides are largely removed by the process. We anticipate that the ability to engineer the surface of AlN films with enhanced precision using isotropic plasma ALE will facilitate applications of AlN in nonlinear photonics and electronics.

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